# **Excellent Integrated System Limited**

Stocking Distributor

Click to view price, real time Inventory, Delivery & Lifecycle Information:

STMicroelectronics PD84006-E

For any questions, you can email us directly: <a href="mailto:sales@integrated-circuit.com">sales@integrated-circuit.com</a>





### PD84006-E

# RF power transistor, LdmoST plastic family N-channel enhancement-mode lateral MOSFETs

Datasheet -production data

#### **Features**

- Excellent thermal stability
- Common source configuration
- Broadband performances: P<sub>OUT</sub> = 6 W with 13 dB gain @ 870 MHz
- Plastic package
- ESD protection
- In compliance with the 2002/95/EC European directive

#### **Description**

The PD84006-E is a common source N-channel, enhancement-mode lateral field-effect RF power transistor. It is designed for high gain, broadband commercial and industrial applications. It operates at 7 V in common source mode at frequencies of up to 1 GHz boasts the excellent gain, linearity and reliability of ST's latest LDMOS technology mounted in the first true SMD plastic RF power package, PowerSO-10RF 's superior linearity performance makes it an ideal solution for portable radio and UHF RFID reader. The PowerSO-10 plastic package, designed to offer high reliability, is the first ST JEDEC approved, high power SMD package. It has been specially optimized for RF needs and offers excellent RF performances and ease of assembly.

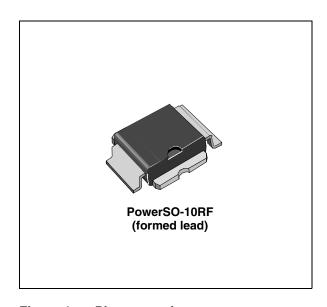


Figure 1. Pin connections

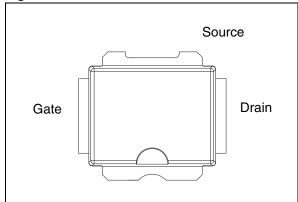


Table 1. Device summary

Order code	Package	Packaging
PD84006-E	PowerSO-10RF (formed lead)	Tube

May 2012 Doc ID 16087 Rev 2 1/11



Contents PD84006-E

### **Contents**

1	Elec	trical data	3
	1.1	Maximum ratings	3
	1.2	Thermal data	3
2	Elec	trical characteristics	4
	2.1	Static	4
	2.2	Dynamic	4
	2.3	ESD protection characteristics	4
3	Туріс	cal performances	5
4	Pack	kage mechanical data	6
5	Revi	ision history	10





PD84006-E Electrical data

### 1 Electrical data

### 1.1 Maximum ratings

 $(T_{CASE} = 25 \, ^{\circ}C)$ 

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V <sub>(BR)DSS</sub>	Drain-source voltage	25	V
V <sub>GS</sub>	Gate-source voltage	-0.5 to +15	V
I <sub>D</sub>	Drain current	5	Α
P <sub>DISS</sub>	Power dissipation (@ T <sub>C</sub> = 70 °C)	59	W
T <sub>J</sub>	Max. operating junction temperature	165	°C
T <sub>STG</sub>	Storage temperature	-65 to +150	°C

#### 1.2 Thermal data

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R <sub>thJC</sub>	Junction - case thermal resistance	1.6	°C/W



#### **Electrical characteristics**

PD84006-E

### 2 Electrical characteristics

 $T_{CASE} = +25 \, ^{\circ}C$ 

### 2.1 Static

Table 4. Static

Symbol		Min	Тур	Max	Unit		
I <sub>DSS</sub>	$V_{GS} = 0V$	V <sub>DS</sub> = 25 V				1	μΑ
I <sub>GSS</sub>	$V_{GS} = 5 V$	V <sub>DS</sub> = 0 V	V <sub>DS</sub> = 0 V			1	μA
V <sub>GS(Q)</sub>	V <sub>DS</sub> = 10 V	I <sub>D</sub> = 150 mA		3.0		4.3	V
V <sub>DS(ON)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 1 A			0.34		V
C <sub>ISS</sub>	V <sub>GS</sub> = 0V	V <sub>DS</sub> = 7 V	f = 1 MHz		40		pF
C <sub>OSS</sub>	V <sub>GS</sub> = 0V	V <sub>DS</sub> = 7 V	f = 1 MHz		33		pF
C <sub>RSS</sub>	V <sub>GS</sub> = 0V	V <sub>DS</sub> = 7 V	f = 1 MHz		1.45		pF

### 2.2 Dynamic

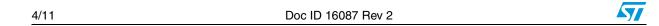
Table 5. Dynamic

Symbol	Test conditions	Min	Тур	Max	Unit
P <sub>3</sub> dB	$V_{DD} = 7.5 \text{ V}, I_{DQ} = 150 \text{ mA}$ f = 870 MHz	5	6		W
G <sub>P</sub>	V <sub>DD</sub> = 7.5 V, I <sub>DQ</sub> = 150 mA, P <sub>OUT</sub> = 2 W, f = 870 MHz	15		_	dB
h <sub>D</sub>	$V_{DD} = 7.5 \text{ V}, I_{DQ} = 150 \text{ mA}, P_{OUT} = P_3 \text{dB}, f = 870 \text{ MHz}$	50	60		%
Load mismatch	$V_{DD} = 9.5 \text{ V}, I_{DQ} = 150 \text{ mA}, P_{OUT} = 8 \text{ W}, f = 870 \text{ MHz}$ All phase angles	20:1			VSWR

### 2.3 ESD protection characteristics

Table 6. ESD protection characteristics

Test conditions	Class
Human body model	2
Machine model	М3



PD84006-E Typical performances

### 3 Typical performances

Figure 2. Output power and efficiency Figure 3. Gain vs. output power vs. frequency Vdd = 7.2 V, Vdd = 7.2 V, Idq = 200 mA

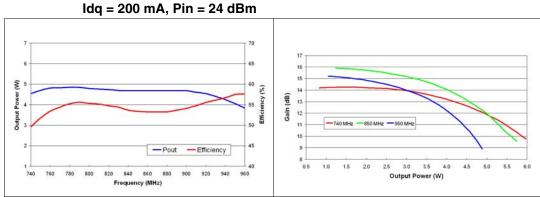


Figure 4. Input return loss vs. frequency Vdd = 7.2 V, Idq = 200 mA

Figure 5. Harmonics vs. frequency Vdd = 7.2 V, Idq = 200 mA, Pin = 24 dBm

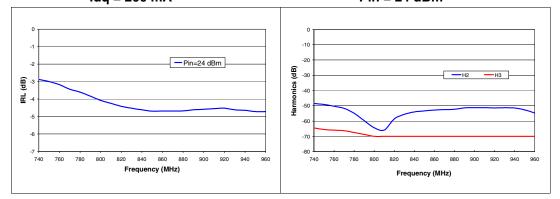
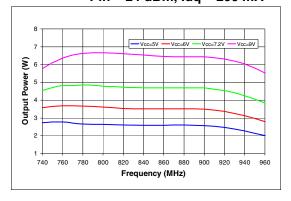


Figure 6. Output power vs. frequency and supply voltage
Pin = 24 dBm, Idq = 200 mA







### Distributor of STMicroelectronics: Excellent Integrated System Limited

Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com

Datasheet of PD84006-E - TRANS N-CH LDMOST PWRSO-10RF

Package mechanical data

PD84006-E

## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: <a href="https://www.st.com">www.st.com</a>. ECOPACK<sup>®</sup> is an ST trademark.





#### PD84006-E

#### Package mechanical data

Table 7. PowerSO-10RF formed lead (gull wing) mechanical data

Dim.		mm.				
	Min	Тур	Max	Min	Тур	Max
A1	0	0.05	0.1	0.	0.0019	0.0038
A2	3.4	3.5	3.6	0.134	0.137	0.142
А3	1.2	1.3	1.4	0.046	0.05	0.054
A4	0.15	0.2	0.25	0.005	0.007	0.009
а		0.2			0.007	
b	5.4	5.53	5.65	0.212	0.217	0.221
С	0.23	0.27	0.32	0.008	0.01	0.012
D	9.4	9.5	9.6	0.370	0.374	0.377
D1	7.4	7.5	7.6	0.290	0.295	0.298
E	13.85	14.1	14.35	0.544	0.555	0.565
E1	9.3	9.4	9.5	0.365	0.37	0.375
E2	7.3	7.4	7.5	0.286	0.292	0.294
E3	5.9	6.1	6.3	0.231	0.24	0.247
F		0.5			0.019	
G		1.2			0.047	
L	0.8	1	1.1	0.030	0.039	0.042
R1			0.25			0.01
R2		0.8			0.031	
Т	2 deg	5 deg	8 deg	2 deg	5 deg	8 deg
T1		6 deg			6 deg	
T2		10 deg			10 deg	

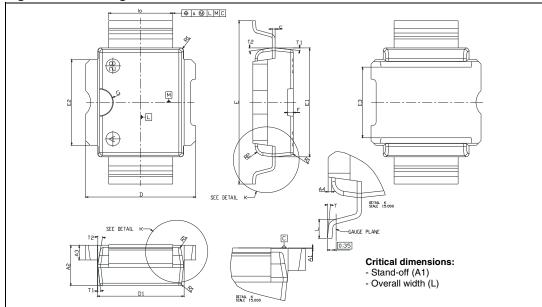
Note: Resin protrusions not included (max value: 0.15 mm per side)



#### Package mechanical data

PD84006-E





Doc ID 16087 Rev 2

#### PD84006-E

#### Package mechanical data

**Tube information** Figure 8. SCALE 5,000 SCALE SCALE 2,000 (9) 0.8±0,1 (\*\*) 5.012.14 17,2±0,2 (\*) € 18,8±0,2 ③ 14,340,2 (\*) 10.1±0.2 (\*)€ a (D) 9.9±0,2 (3) Marking area 'PART 1' (2) (B) (E) 0.65 (\*) CRITICAL DIMENSIONS 3±0,2 (\*) 10,000 10±2,5 SCALE 0



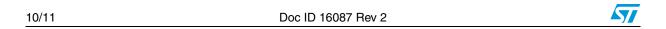


Revision history PD84006-E

# 5 Revision history

Table 8. Document revision history

Date	Revision	Changes		
07-Aug-2009	1	Initial release.		
23-May-2012	2	Updated V <sub>GS(Q)</sub> in <i>Table 4: Static</i> .		





# Distributor of STMicroelectronics: Excellent Integrated System Limited Datasheet of PD84006-E - TRANS N-CH LDMOST PWRSO-10RF

Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com

#### PD84006-E

#### Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN WRITING BY TWO AUTHORIZED ST REPRESENTATIVES, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER'S OWN RISK.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2012 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Philippines - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com

